FIG.1

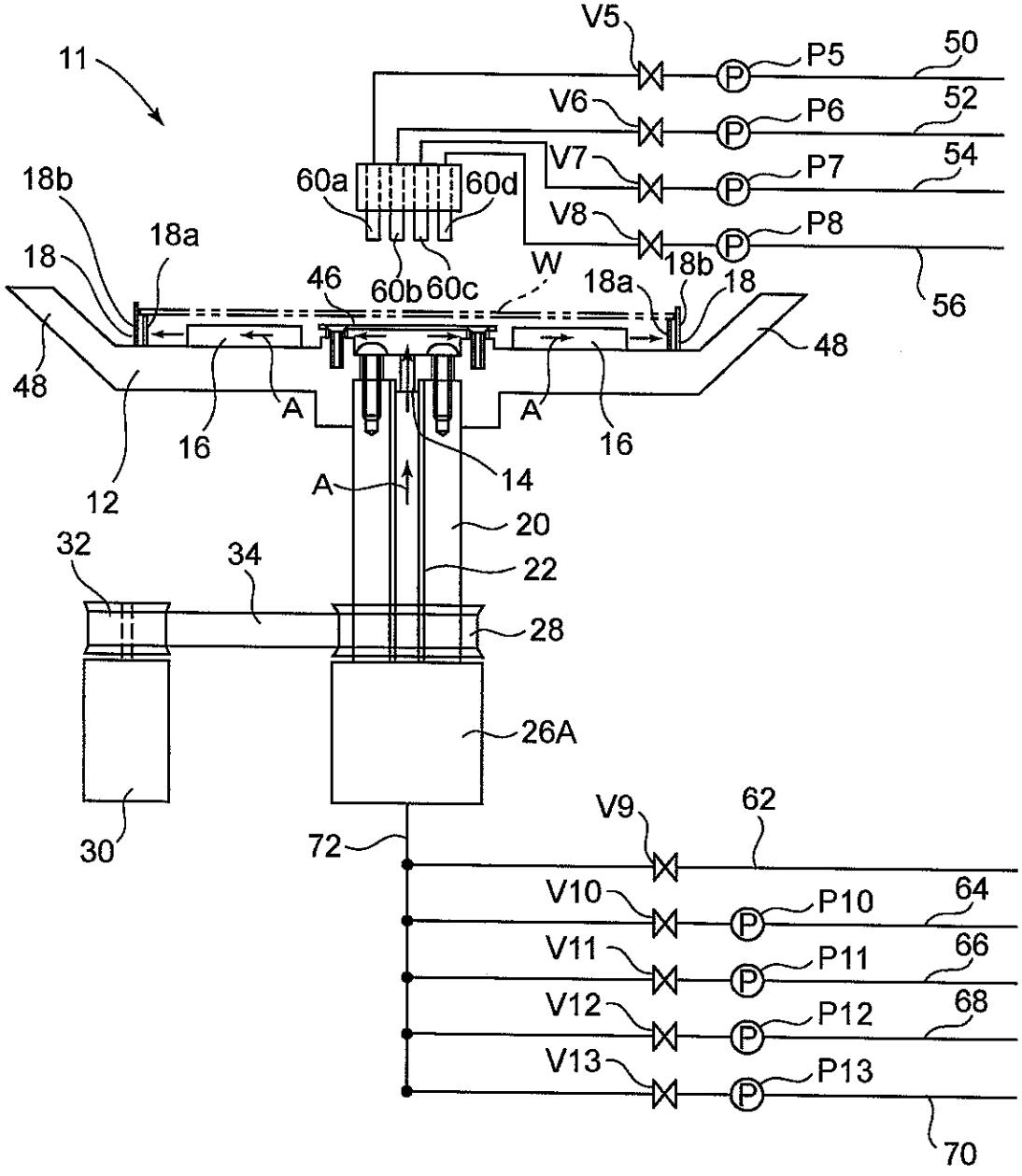

11
V5
P5
50
V6
P6
52
V7
P7
54
V8
P8
56
60a
60d
60b
60c
W
18b
18a
18
46
48
A
16
12
14
20
22
28
26A
32
34
30
72
V9
62
V10
P10
64
V11
P11
66
V12
P12
68
V13
P13
70

FIG.2

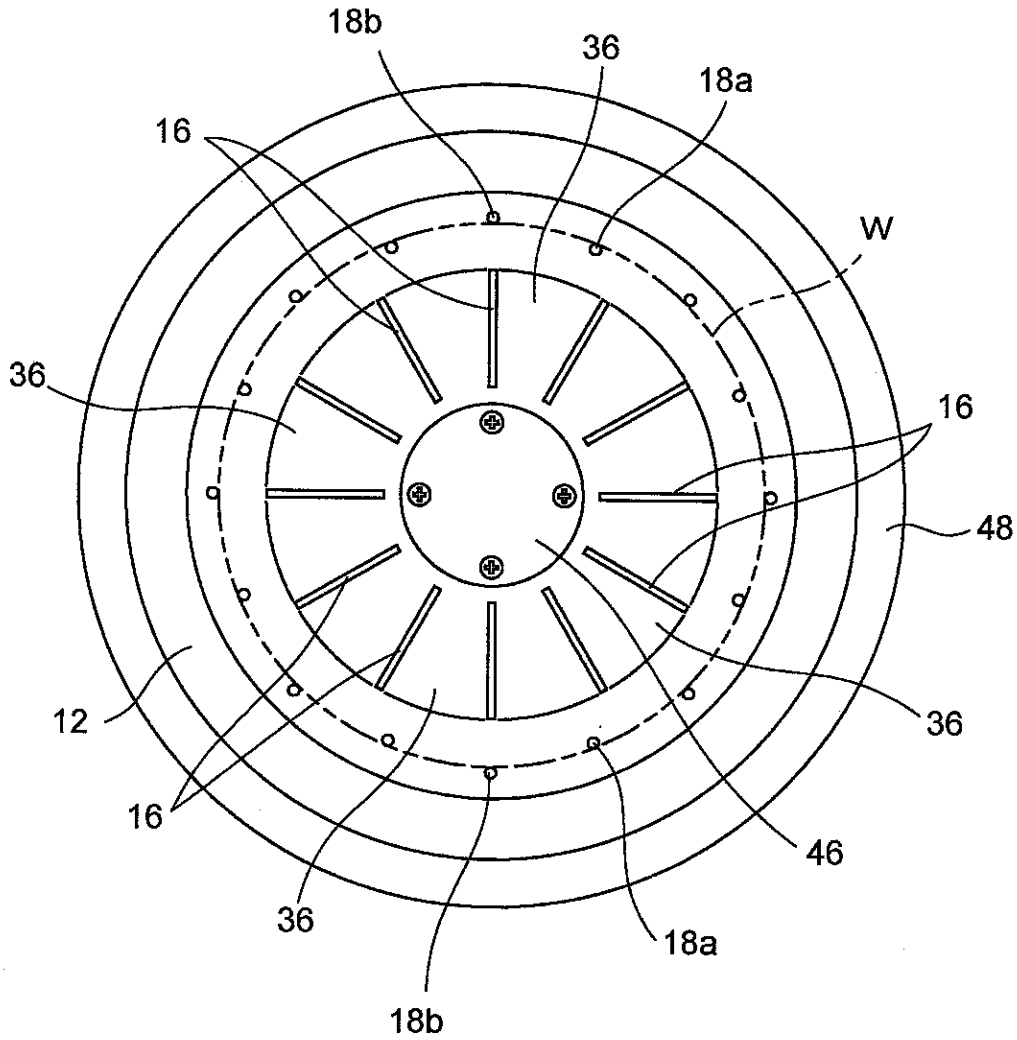


FIG.3

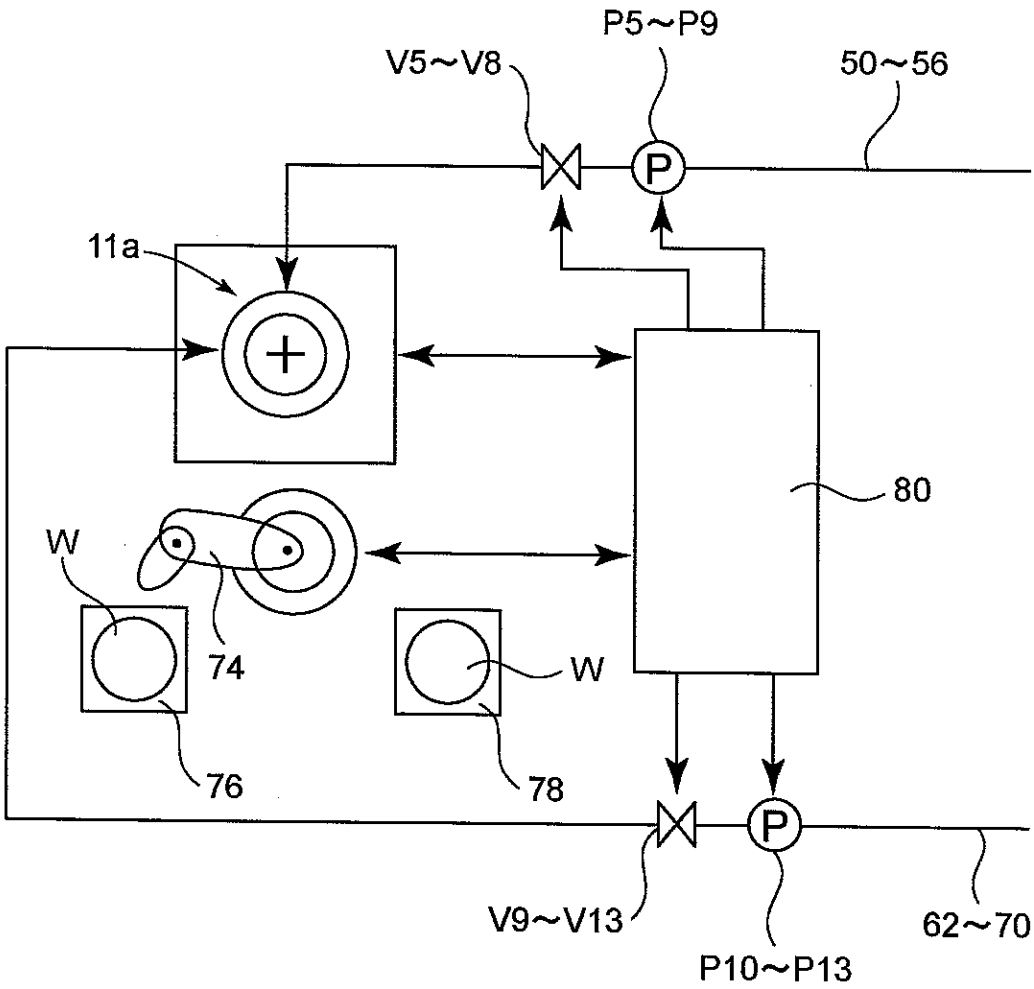


FIG.4

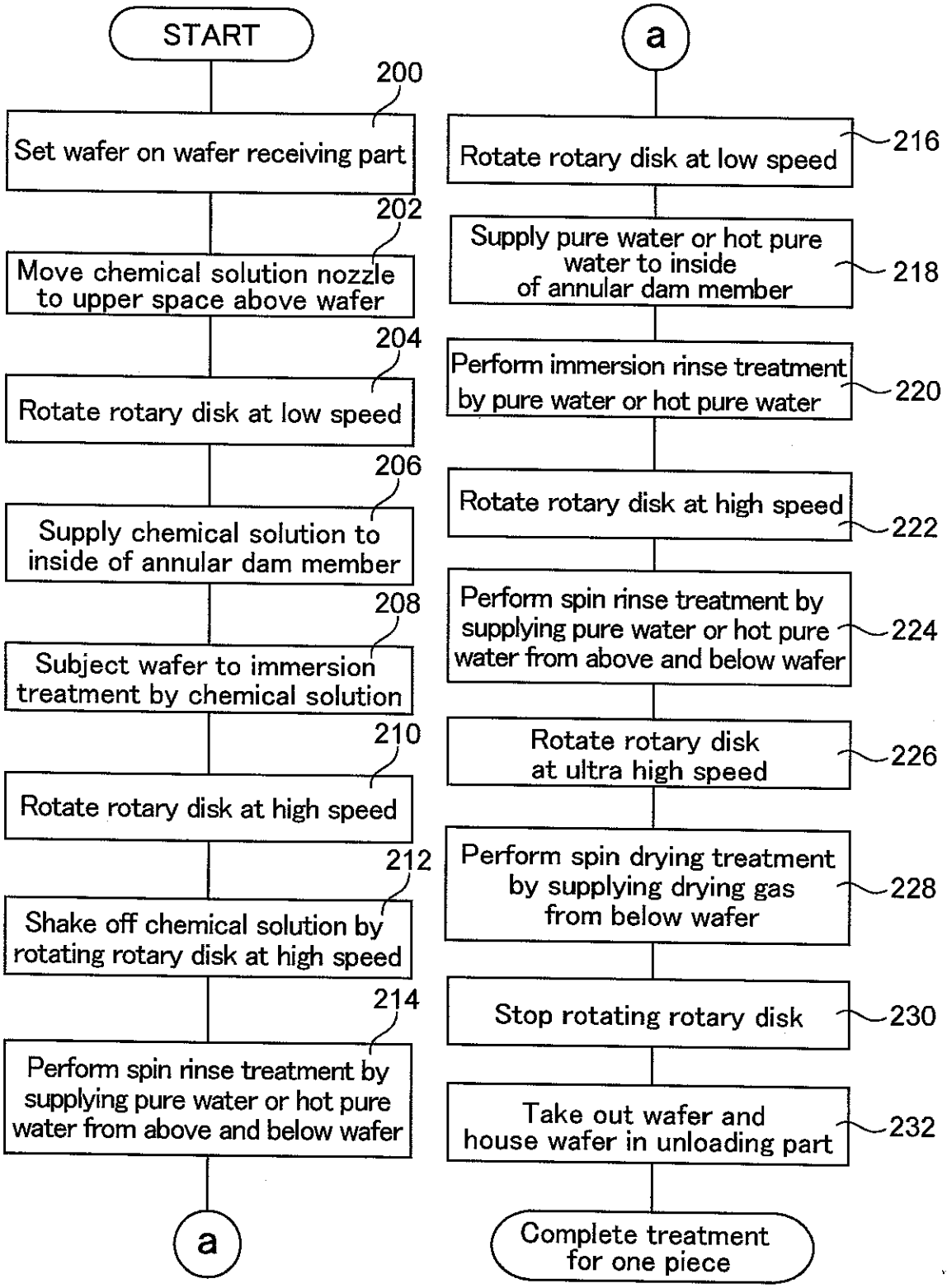

START
200
Set wafer on wafer receiving part
202
Move chemical solution nozzle to upper space above wafer
204
Rotate rotary disk at low speed
206
Supply chemical solution to inside of annular dam member
208
Subject wafer to immersion treatment by chemical solution
210
Rotate rotary disk at high speed
212
Shake off chemical solution by rotating rotary disk at high speed
214
Perform spin rinse treatment by supplying pure water or hot pure water from above and below wafer
a
a
216
Rotate rotary disk at low speed
218
Supply pure water or hot pure water to inside of annular dam member
220
Perform immersion rinse treatment by pure water or hot pure water
222
Rotate rotary disk at high speed
224
Perform spin rinse treatment by supplying pure water or hot pure water from above and below wafer
226
Rotate rotary disk at ultra high speed
228
Perform spin drying treatment by supplying drying gas from below wafer
230
Stop rotating rotary disk
232
Take out wafer and house wafer in unloading part
Complete treatment for one piece

FIG.5

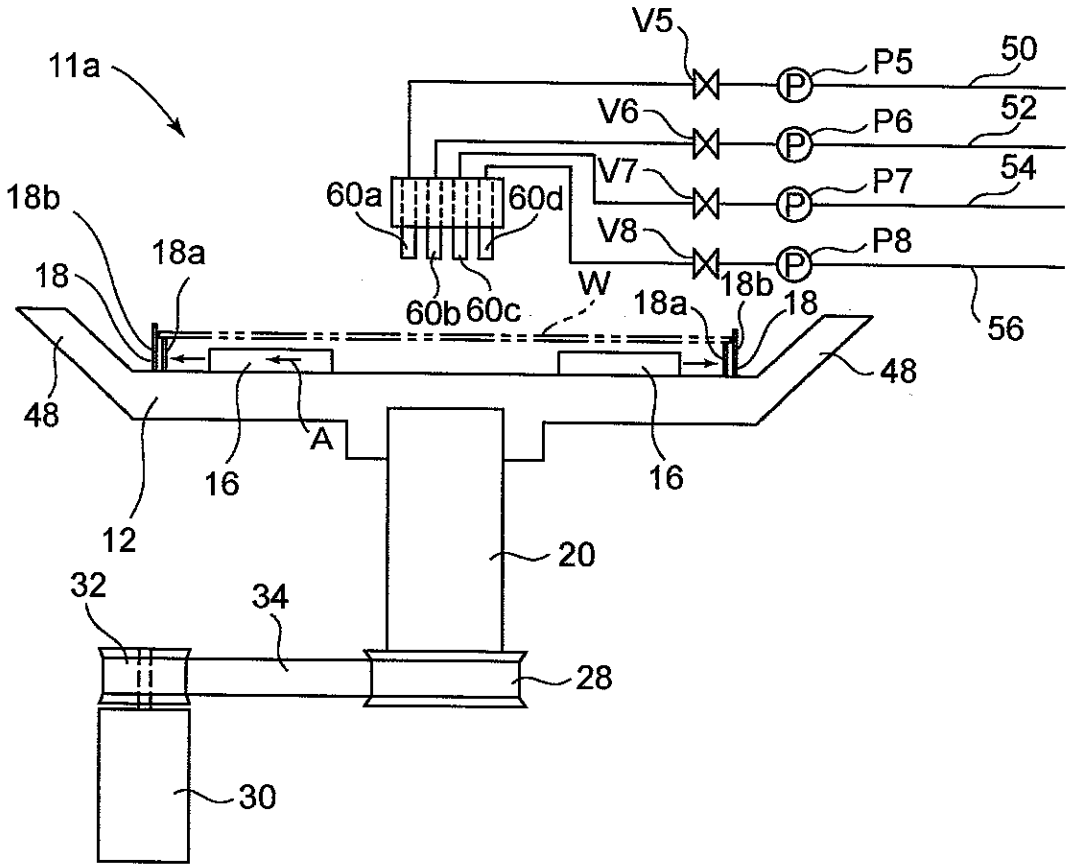

11a
V5
P5
50
V6
P6
52
V7
P7
54
V8
P8
56
60a
60d
60b
60c
W
18b
18a
18
48
A
16
12
20
32
34
28
30

FIG.6

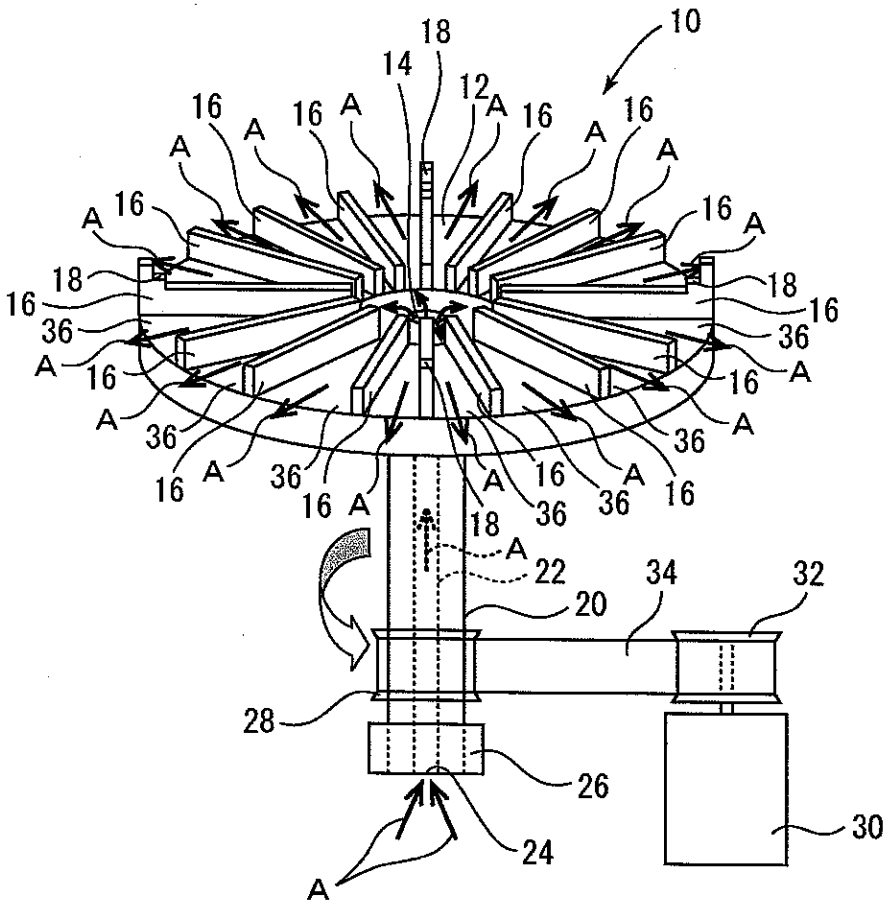


FIG.7

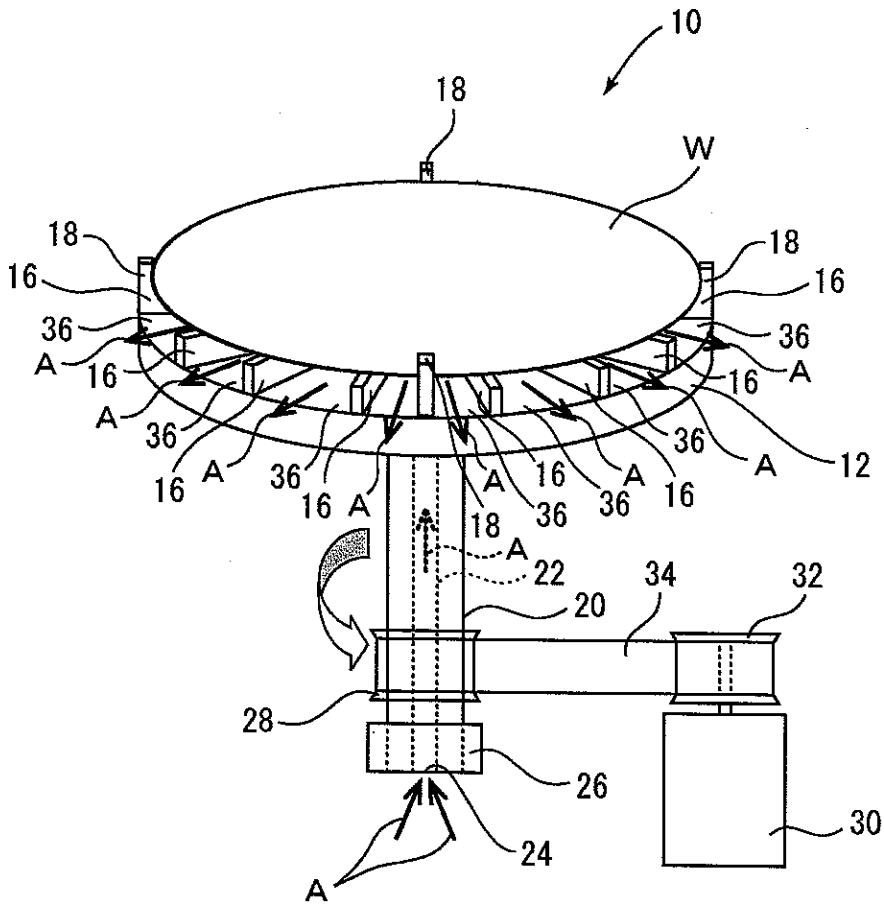


FIG.8

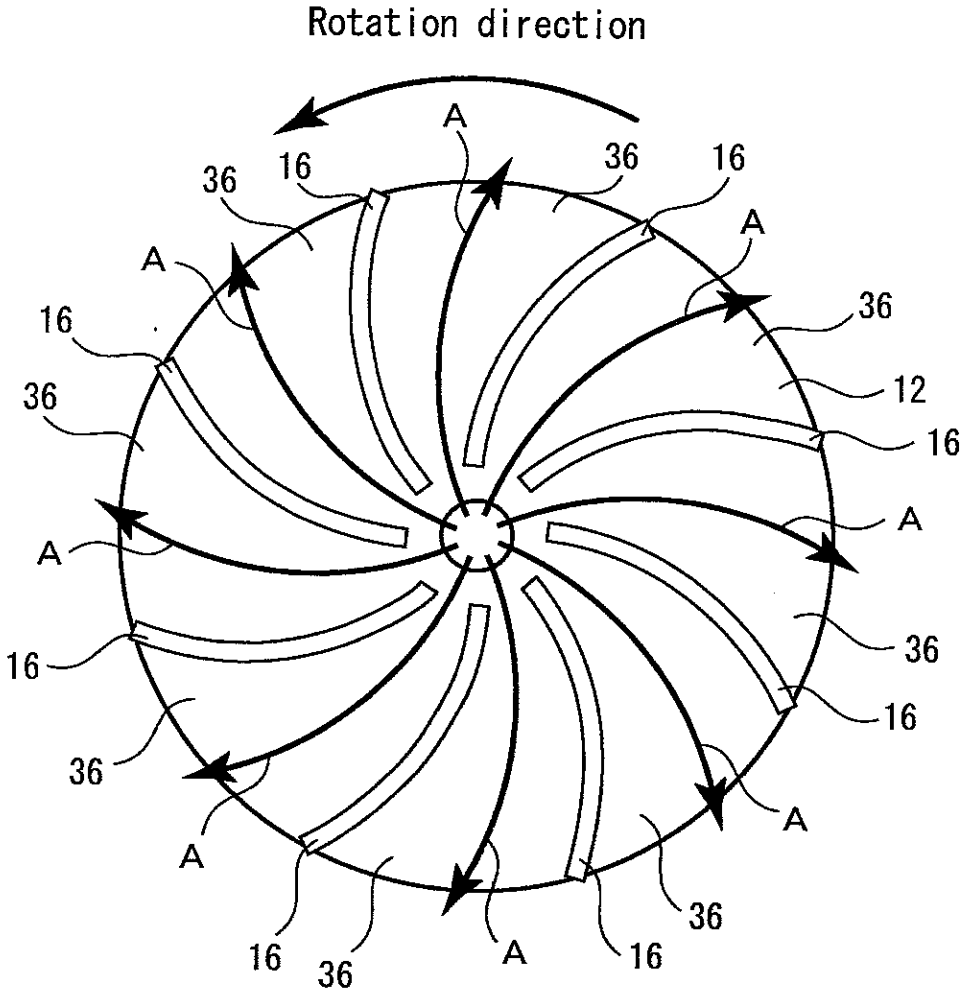

Rotation direction
A
36
16
A
36
16
A
36
12
16
A
36
16
A
36
16
A
36
16
A
36
16
A
36
16
A
36
16
A

FIG.9

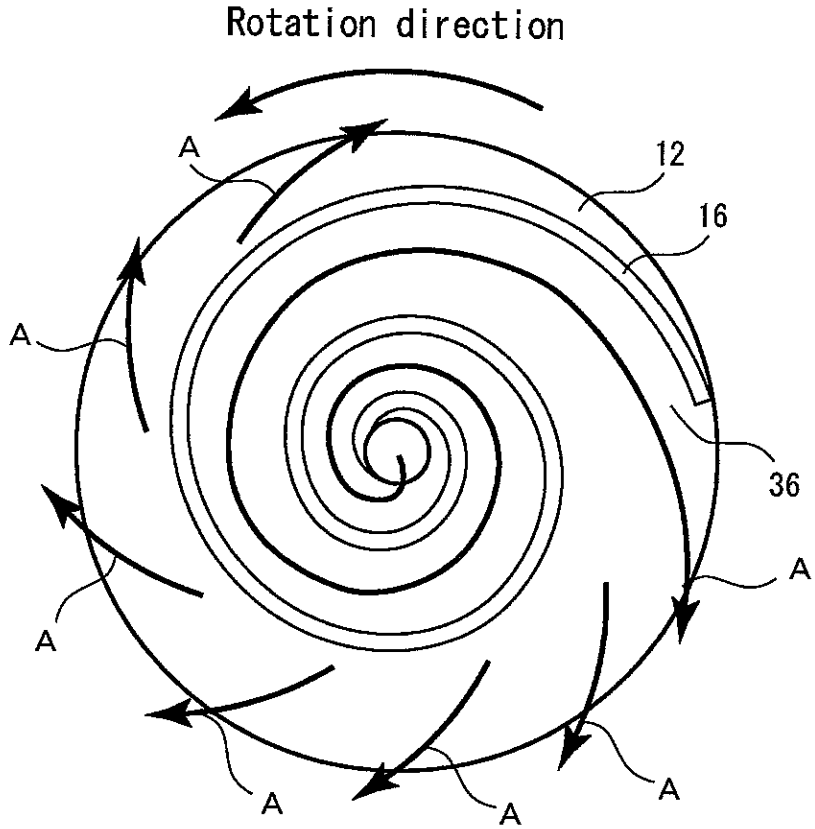
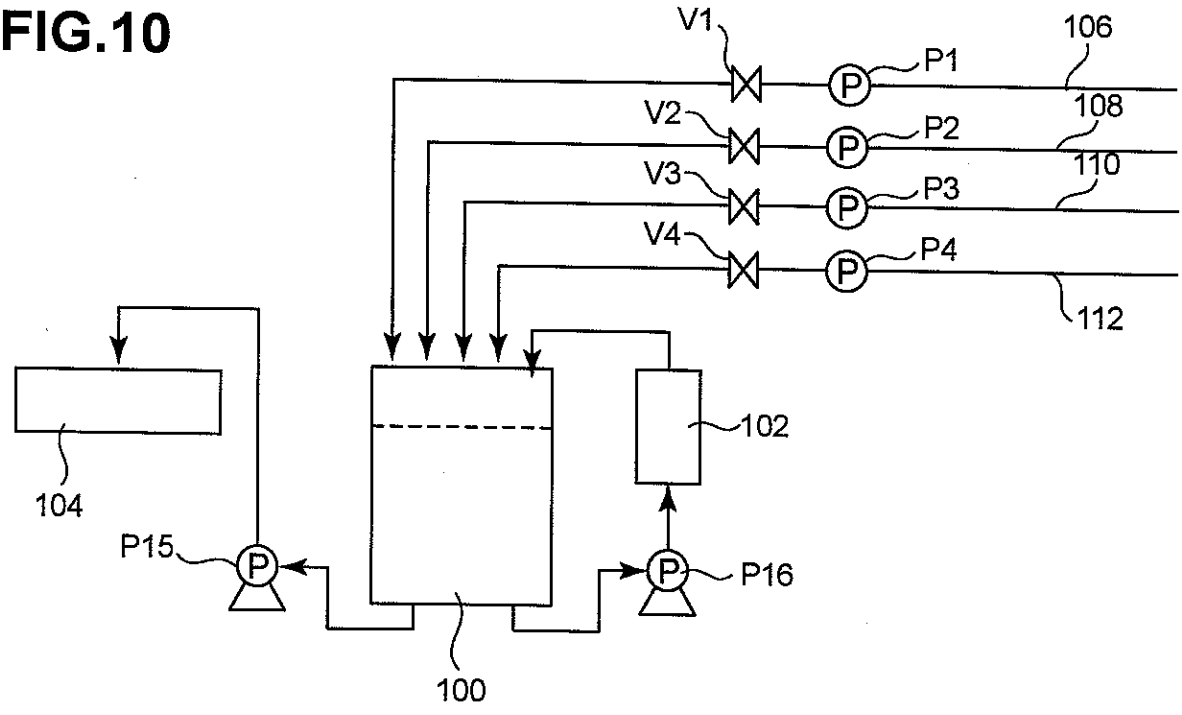

Rotation direction
A
12
16
A
36
A
A
A
A
A

FIG.10


V1
P1
106
V2
P2
108
V3
P3
110
V4
P4
112
102
104
P15
P16
100